

Title (en)

Method of producing a transparent photocathode.

Title (de)

Verfahren zum Herstellen einer Durchsichtphotokathode.

Title (fr)

Procédé de fabrication d'une photocathode transparente.

Publication

EP 0211168 A1 19870225 (DE)

Application

EP 86107082 A 19860524

Priority

DE 3524765 A 19850711

Abstract (en)

[origin: US4713353A] A method of producing a transparent photocathode comprises applying a multi-layer wafer to a carrier service so that the wafer projects beyond the carrier on all sides, effecting a chemical denudation on the substrate and after the chemical denudation on the substrate removing at least the overhanging parts of the multi-layer wafer mechanically. Chemical denudations are advantageously made by etching. The substrate comprises a gallium arsenide. The subsequent layers in the active photocathode semiconductor layer are applied by an epitaxial process.

Abstract (de)

Zur Erzielung einer exakten Randbegrenzung einer Durchsichtphotokathode wird vorgeschlagen, auf den Kathodenträger (6) eine Halbleiterscheibe mit einem überstehenden Rand (7) anzubringen und diesen nach Abätzen der Substratschicht (1) mechanisch zu entfernen.

IPC 1-7

H01J 9/12; **H01L 21/302**

IPC 8 full level

H01J 9/12 (2006.01); **H01J 29/38** (2006.01); **H01L 21/302** (2006.01)

CPC (source: EP US)

H01J 9/12 (2013.01 - EP US); **H01J 29/38** (2013.01 - EP US); **H01J 2201/3423** (2013.01 - EP US)

Citation (search report)

- DE 2550056 A1 19760526 - VARIAN ASSOCIATES
- DE 1233948 B 19670209 - ITT IND GMBH
- DE 2613490 B2 19780413
- DE 2517159 B2 19770217

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DOCDB simple family (publication)

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DOCDB simple family (application)

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